

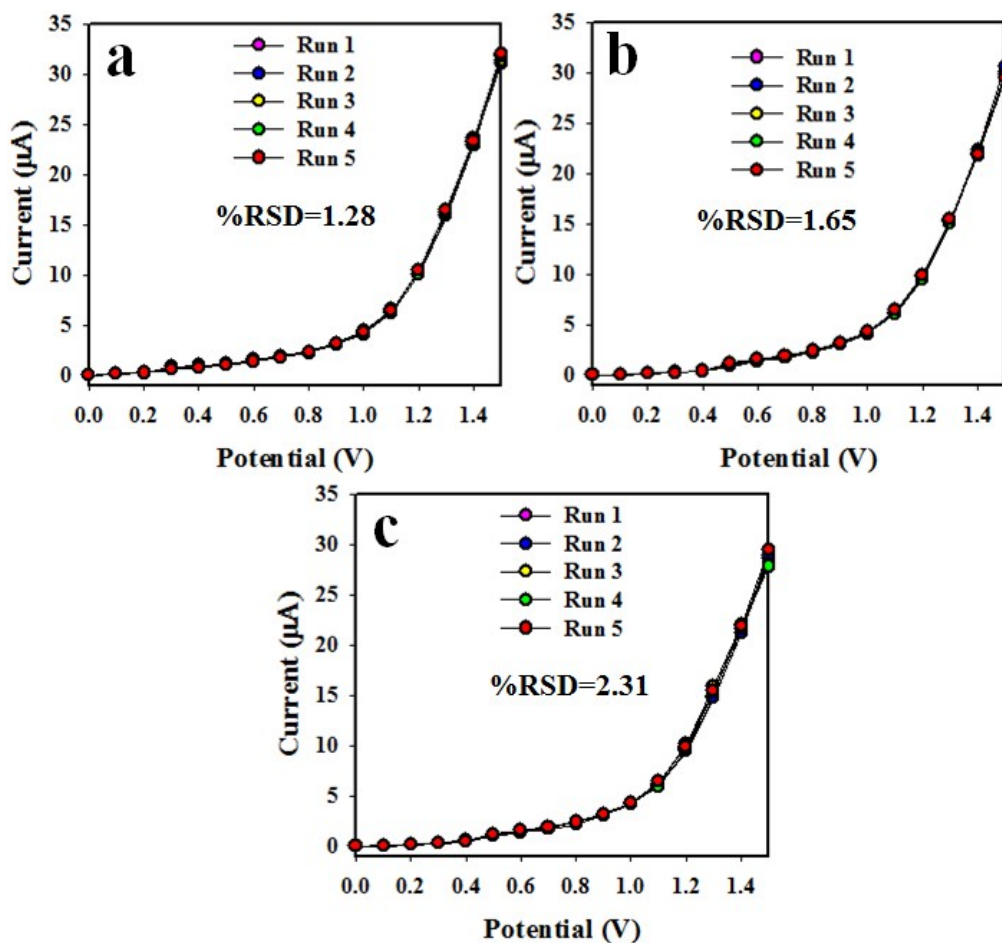
## 2-Nitrophenol sensor based wet-chemically prepared binary doped $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$ nanosheets by electrochemical approach

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### Supporting information

Optimization of 2-Nitrophenol chemical sensor (Intra-day):



**Fig. S1** Optimization of 2-Nitrophenol chemical sensor based on  $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$  NSs, (a) repeatability at 0 hour, (b) repeatability after 2 hour, and (c) repeatability after 4 hours,

Optimization of 2-Nitrophenol chemical sensor (Inter-day):

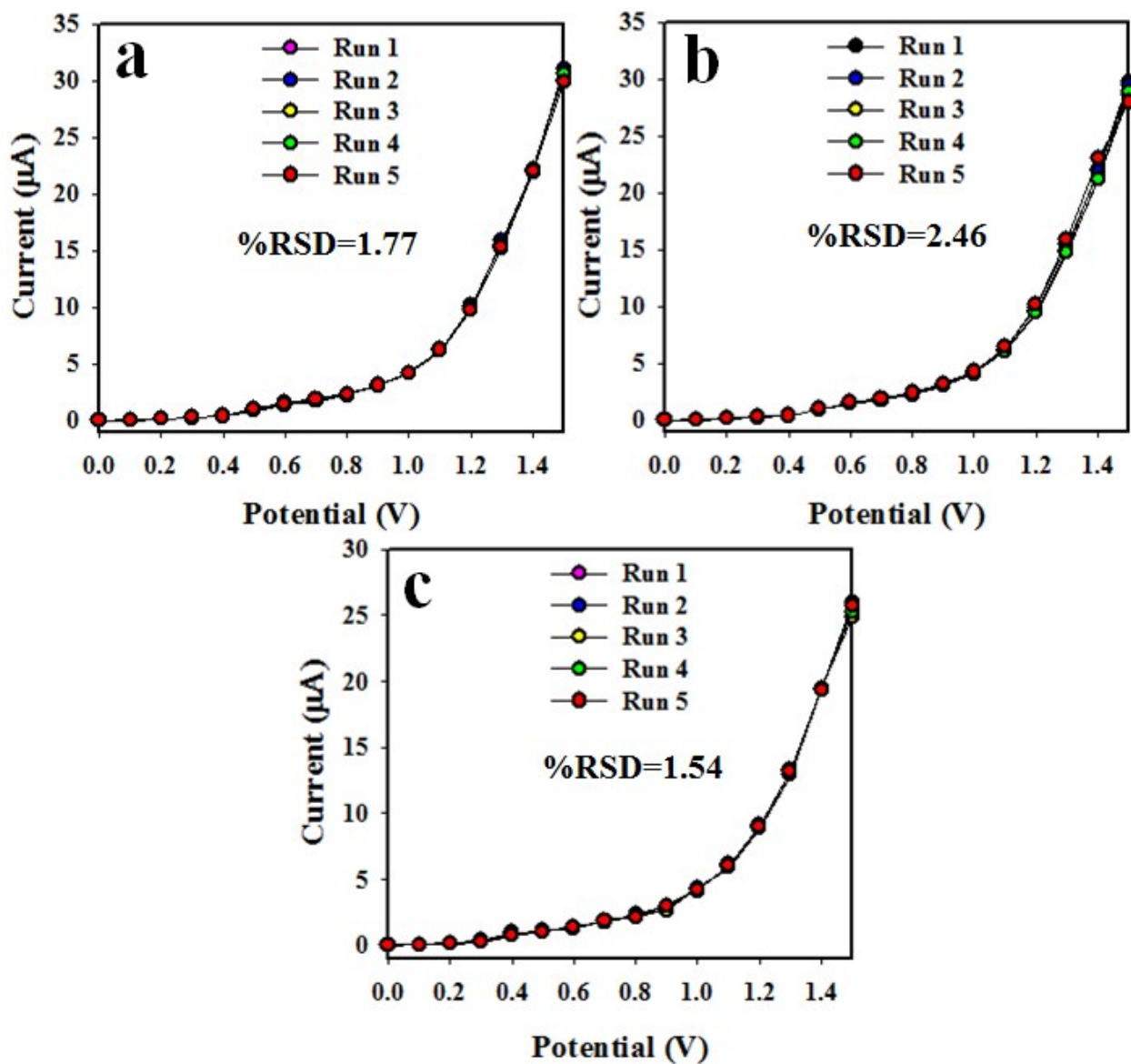
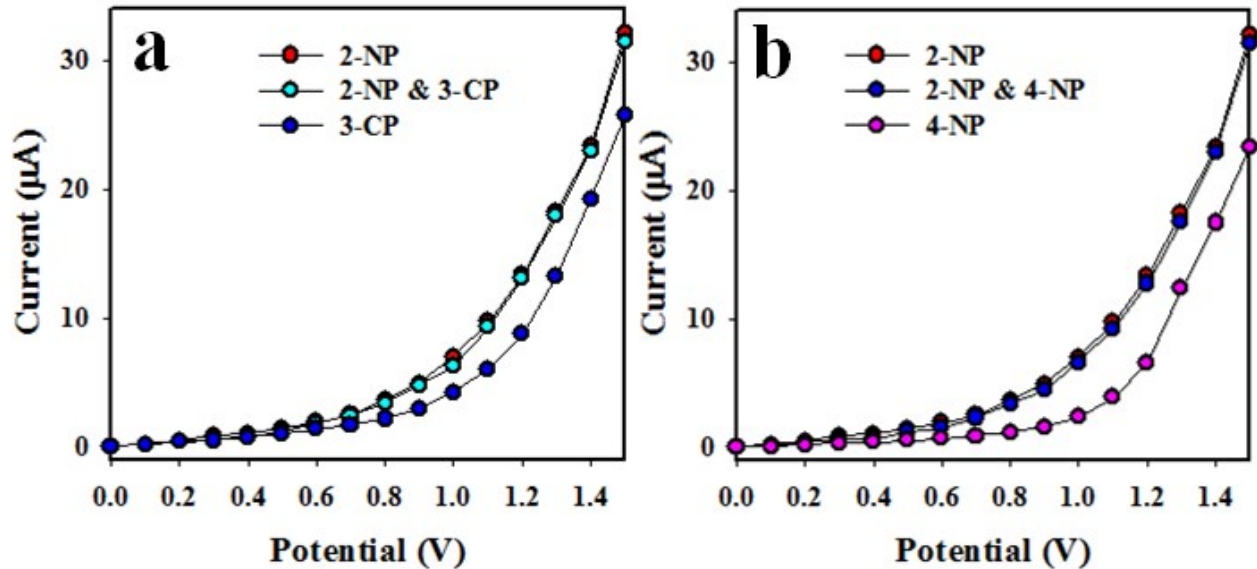


Fig. S2 Optimization of 2-Nitrophenol chemical sensor based on  $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$  NSs, (a) repeatability at beginning day, (b) repeatability at 2<sup>nd</sup> day, and (c) repeatability after 3<sup>rd</sup> day,

*Electrochemical responses in mixtures:*



**Fig. S3** The reliable control measurements of 2-NP based on Co<sub>3</sub>O<sub>4</sub>/Al<sub>2</sub>O<sub>3</sub> NSs/GCE, (a) I-V responses in mixed or single target chemicals such as 2-NP, 2-NP+3-CP and 3-CP, (b) I-V responses in mixed or single target chemicals such as 2-NP, 2-NP+4-NP and 4-NP.

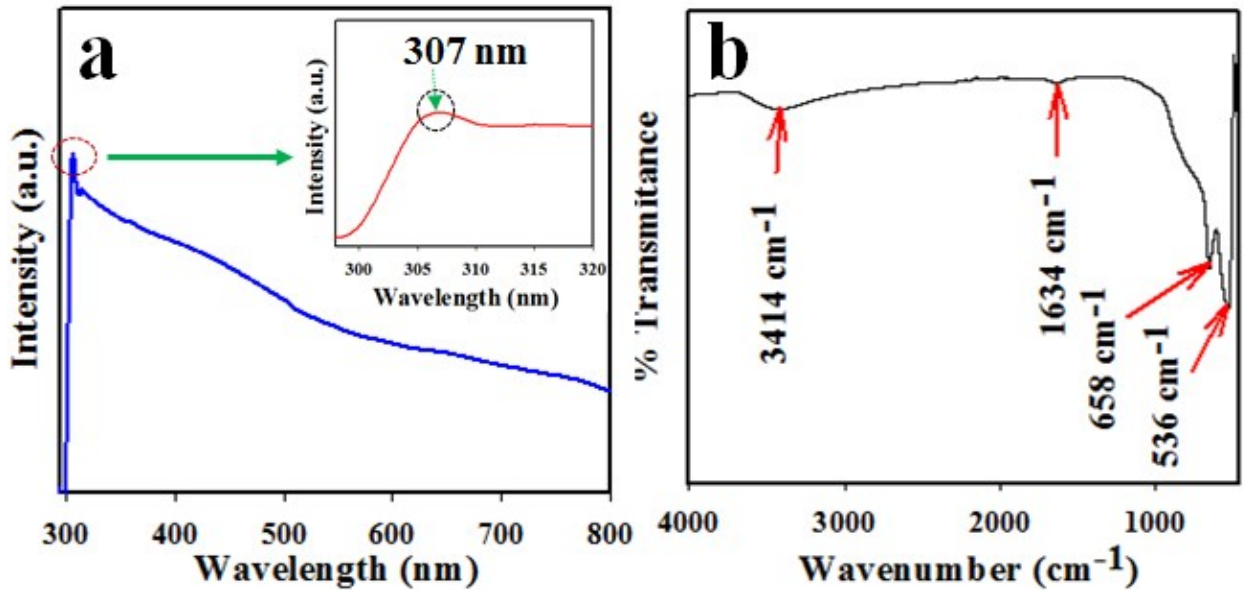
*Optical evaluations:*

The photosensitivity of prepared NSs of Co<sub>3</sub>O<sub>4</sub>/Al<sub>2</sub>O<sub>3</sub> were investigated by UV-vis analysis, which is illustrated in **Fig. S4a**. The UV-vis spectrum is a characteristic of the absorption of radiant energy of visible light and the transition of the outer electrons of the atoms from lower to higher energy level.<sup>1</sup> In this work, the UV absorption study is performed in the range of 290 to 800 nm at room temperature. The resulted spectrum contains a wider and intense peak at 307 nm (an enlarged view is shown in the inset of **Fig. S4a** and this is the characteristic band of synthesized Co<sub>3</sub>O<sub>4</sub>/Al<sub>2</sub>O<sub>3</sub> NSs. The obtained UV absorption band is authenticated for the transition of valance electron of prepared NSs from lower to higher energy level.<sup>2-4</sup> According to the equation (6); the calculated band gape energy is 4.04 eV.

$$E_{bg} = 1240 / \lambda_{max} \quad (6)$$

Here,  $E_{bg}$  = band-gap energy,  $\lambda_{max}$  = maximum absorbed wave length.<sup>5,6</sup>

To identify the functional groups existing in the prepared NSs, the  $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$  NSs were investigated by Fourier-transform infrared (FTIR) spectroscopy, which is presented in **Fig. S4b**. The FTIR is performed at range of  $450\text{--}4000\text{ cm}^{-1}$  and resultant peaks are obtained from the corresponding atomic or molecular vibration. As it is seen in FTIR spectrum, the several major peaks at  $536$ ,  $658$ ,  $1634$  and  $3414\text{ cm}^{-1}$  are observed. The two major peaks at  $536$  and  $658\text{ cm}^{-1}$  are associated to the stretching vibrations of  $\text{Co-O}$ . This observation is consistent with those reported by previous authors.<sup>7-9</sup> The peaks at  $1634$  and  $3400\text{ cm}^{-1}$  are assigned to  $\text{O-H}$  stretching vibration mode<sup>10-13</sup> due to the adsorption of water from environment.



**Fig. S4.** Optical characterization of doped  $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$  nanomaterials. (a) UV/vis. Spectroscopy and (b) FTIR spectroscopy

## XPS analysis of doped $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$ nanomaterials:

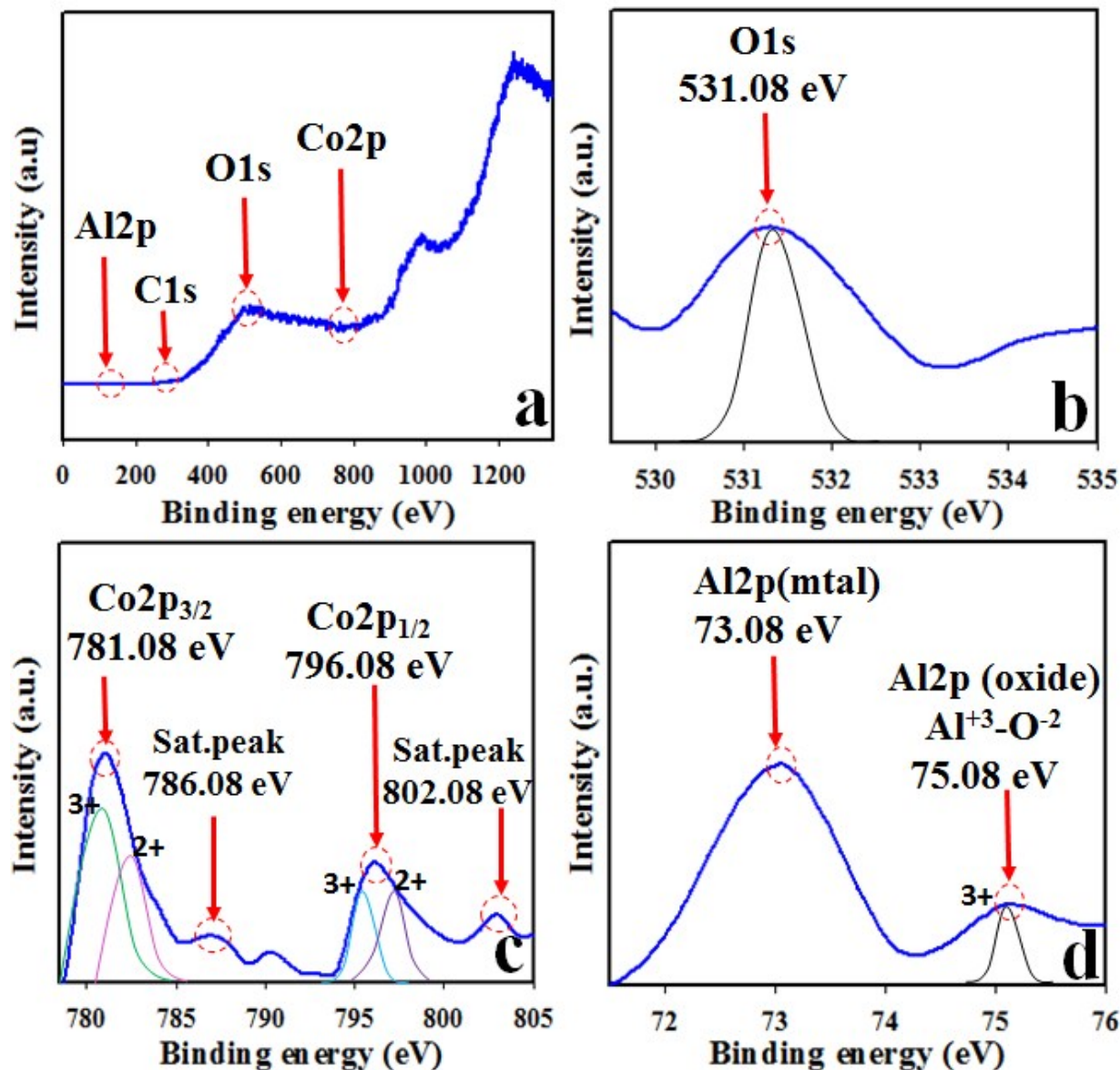


Fig. S5. XPS analysis of doped  $\text{Co}_3\text{O}_4/\text{Al}_2\text{O}_3$  nanomaterials

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